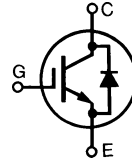


High Voltage IGBT with Diode

Combi Pack
Short Circuit SOA Capability

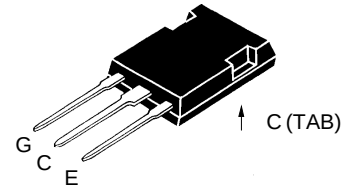
IXSX 35N120AU1

$$\begin{aligned} V_{CES} &= 1200 \text{ V} \\ I_{C25} &= 70 \text{ A} \\ V_{CE(SAT)} &= 4 \text{ V} \end{aligned}$$



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1200	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	70	A
I_{C90}	$T_C = 90^\circ\text{C}$	35	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	140	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_J = 125^\circ\text{C}, R_G = 22 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 70$ @ $0.8 V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = 15 \text{ V}, V_{CE} = 720 \text{ V}, T_J = 125^\circ\text{C}$ $R_G = 22 \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	300 190	W W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
Weight	TO-247 HL	6	g

**PLUS TO-247™
(IXSX35N120AU1)**



G = Gate,
E = Emitter,
C = Collector,
TAB = Collector

Features

- Hole-less TO-247 package for clip mounting
- High frequency IGBT and anti-parallel FRED in one package
- Low $V_{CE(sat)}$
 - for minimum on-state conduction losses
- MOS Gate turn-on
 - drive simplicity
- Fast Recovery Epitaxial Diode (FRED)
 - soft recovery with low I_{RM}

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

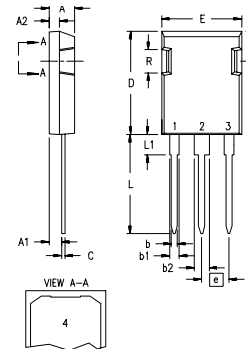
Advantages

- Space savings (two devices in one package)
- Reduces assembly time and cost
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 5 \text{ mA}, V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 4 \text{ mA}, V_{CE} = V_{GE}$	4		8 V
$I_{CES} \text{ ①}$	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$			750 μA 15 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$			4 V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}$; $V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	20	26	S
$I_{C(on)}$	$V_{GE} = 15\text{ V}$, $V_{CE} = 10\text{ V}$		170	A
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		3900	pF
C_{oes}			295	pF
C_{res}			60	pF
Q_g	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		150	nC
Q_{ge}			40	nC
Q_{gc}			70	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = 2.7\text{ }\Omega$ Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G		80	ns
t_{ri}			150	ns
$t_{d(off)}$			400	900 ns
t_{fi}			500	700 ns
E_{off}			10	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = 2.7\text{ }\Omega$ Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G		80	ns
t_{ri}			150	ns
E_{on}			8	mJ
$t_{d(off)}$			400	ns
t_{fi}			700	ns
E_{off}			15	mJ
R_{thJC}				0.42 K/W
R_{thCK}			0.15	K/W

PLUS247™ (IXSX)



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_F	$I_F = I_{C90}$, $V_{GE} = 0\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$, $T_J = 125^\circ\text{C}$			2.35 V
I_{RM}	$I_F = I_{C90}$, $V_{GE} = 0\text{ V}$, $-di_F/dt = 480\text{ A}/\mu\text{s}$ $V_R = 540\text{ V}$ $I_F = 1\text{ A}$; $-di/dt = 200\text{ A}/\mu\text{s}$; $V_R = 30\text{ V}$		32	36 A
t_{rr}			225	ns
t_{rr}			40	60 ns
R_{thJC}				0.65 K/W

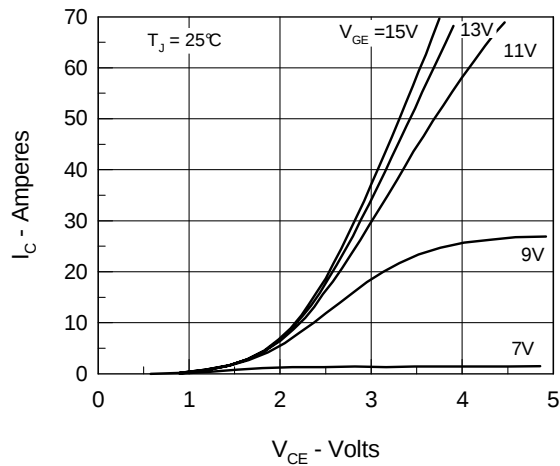
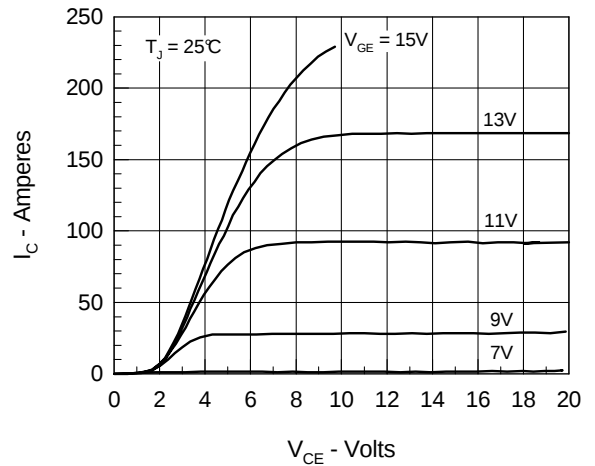
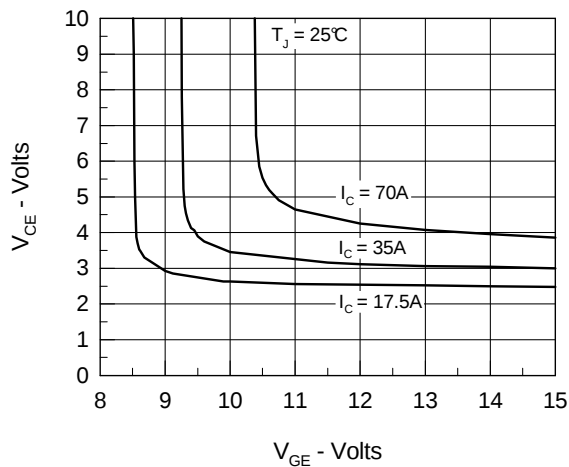
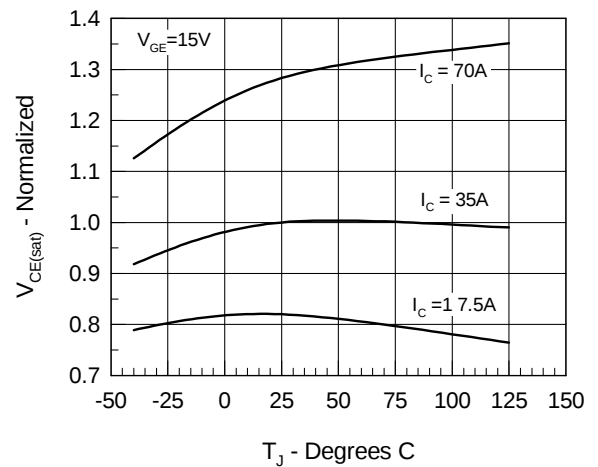
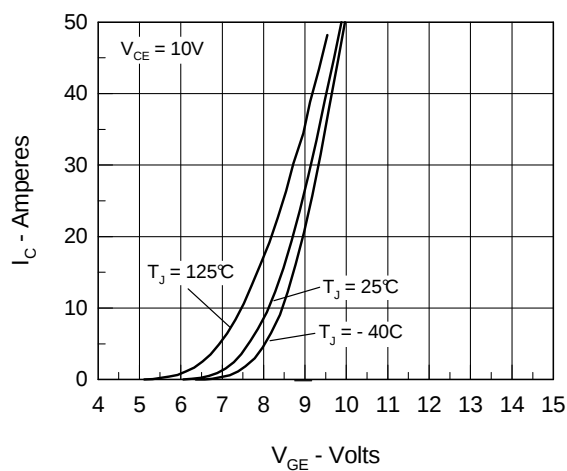
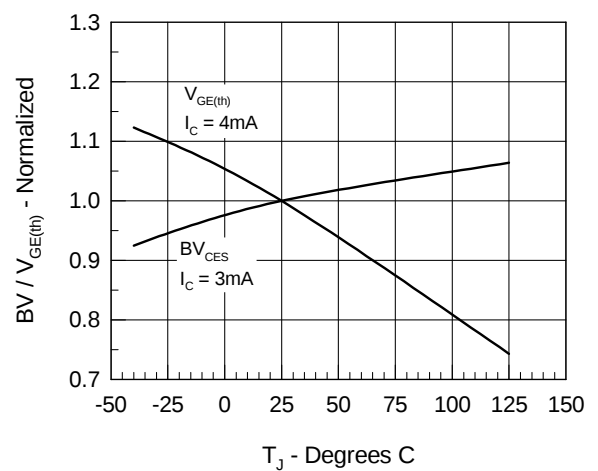
Fig.1 Saturation Characteristics

Fig.2 Output Characteristics

Fig.3 Collector-Emitter Voltage vs. Gate-Emitter Voltage

Fig.4 Temperature Dependence of Output Saturation Voltage

Fig.5 Input Admittance

Fig.6 Temperature Dependence of Breakdown and Threshold Voltage


Fig.7 Turn-Off Energy per Pulse and Fall Time on Collector Current

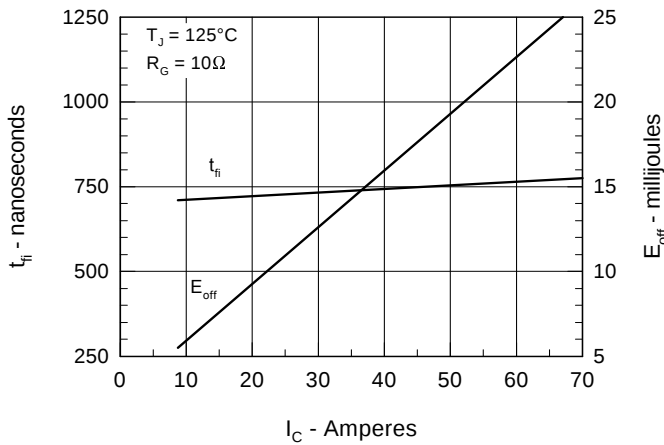


Fig.8 Dependence of Turn-Off Energy Per Pulse and Fall Time on R_G

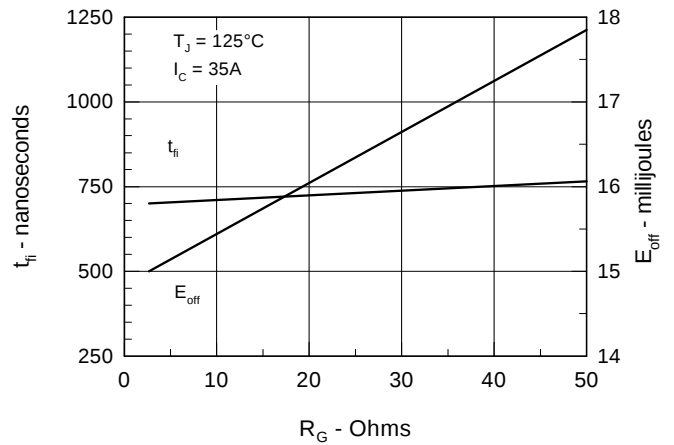


Fig.9 Gate Charge Characteristic Curve

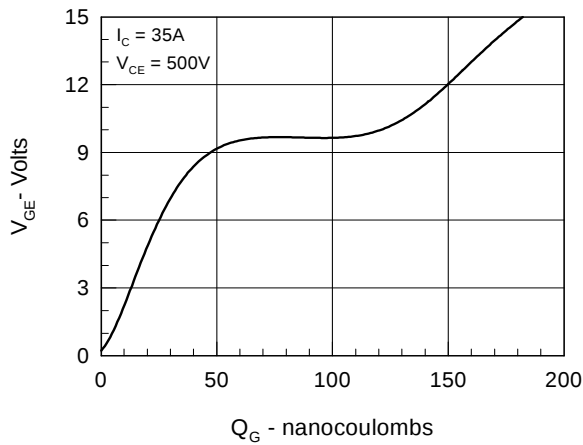


Fig.10 Turn-Off Safe Operating Area

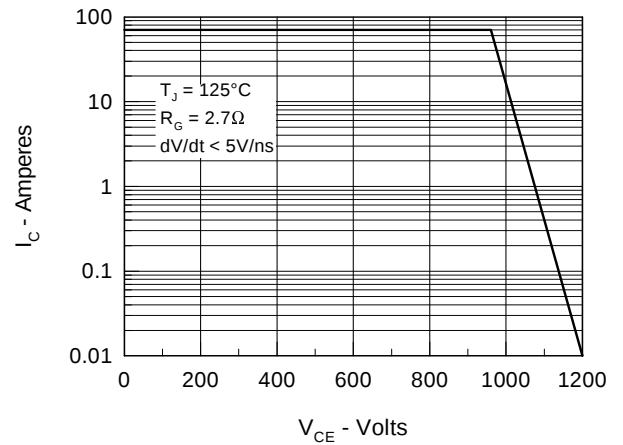


Fig.11 Transient Thermal Impedance

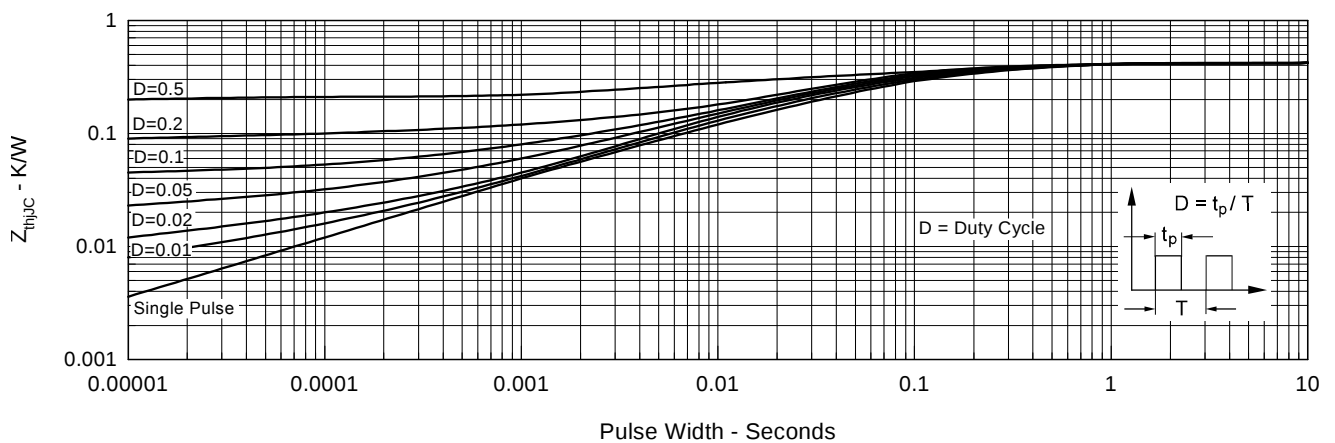
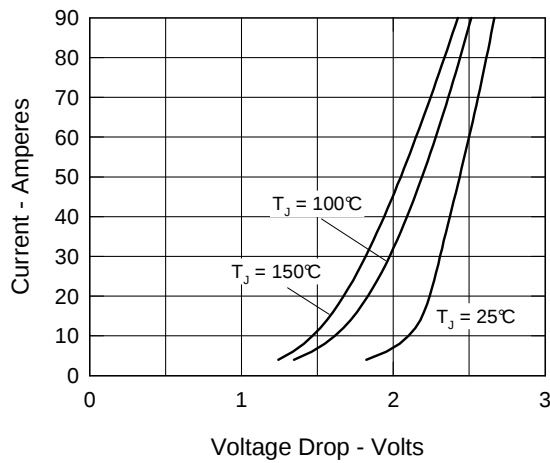
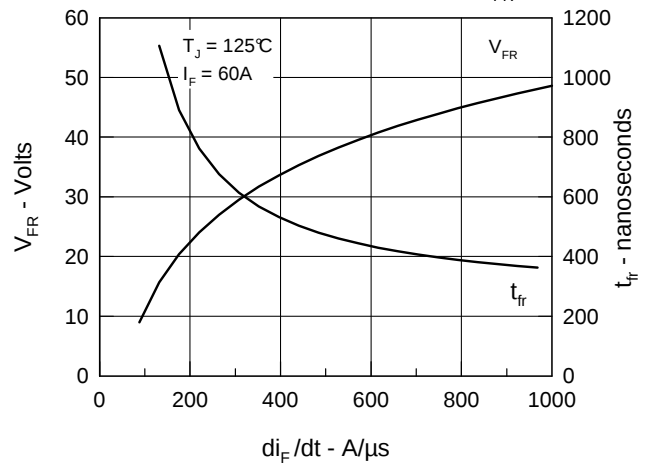
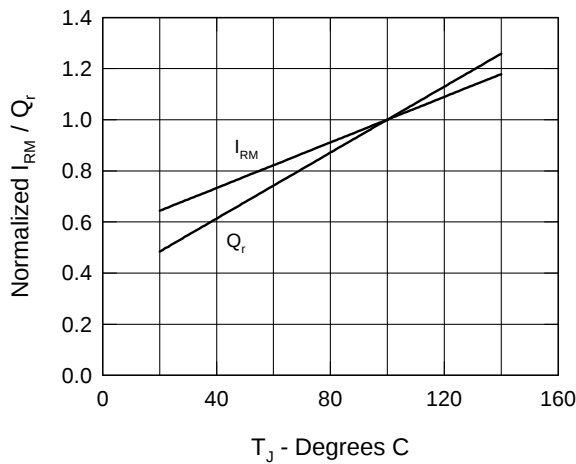
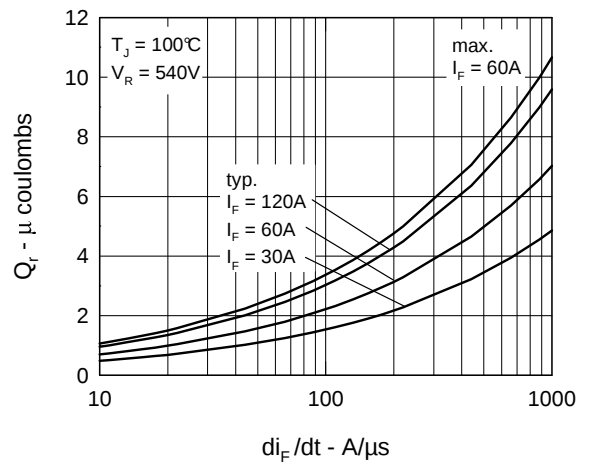
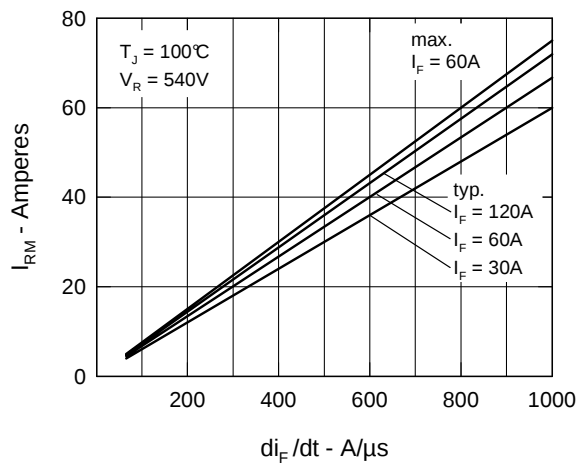


Fig.12 Maximum Forward Voltage Drop

Fig.13 Peak Forward Voltage V_{FR} and Forward Recovery Time t_{FR}

Fig.14 Junction Temperature Dependence off I_{RM} and Q_r

Fig.15 Reverse Recovery Charge

Fig.16 Peak Reverse Recovery Current

Fig.17 Reverse Recovery Time
